

SBAS103C - SEPTEMBER 2000 - REVISED OCTOBER 2006

12-Bit, 4-Channel Parallel Output Sampling ANALOG-TO-DIGITAL CONVERTER

FEATURES

- SINGLE SUPPLY: 2.7V to 5V
- 4-CHANNEL INPUT MULTIPLEXER
- UP TO 200kHz SAMPLING RATE
- FULL 12-BIT PARALLEL INTERFACE
- ±1LSB INL AND DNL
- NO MISSING CODES
- 72dB SINAD
- LOW POWER: 2mW
- SSOP-28 PACKAGE

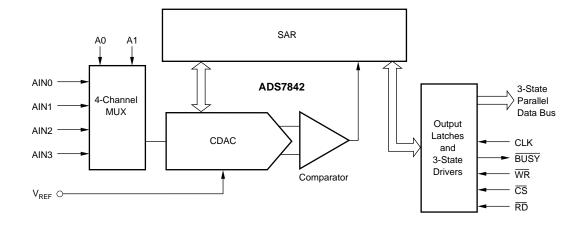
APPLICATIONS

- DATA ACQUISITION
- TEST AND MEASUREMENT
- INDUSTRIAL PROCESS CONTROL
- MEDICAL INSTRUMENTS
- LABORATORY EQUIPMENT

DESCRIPTION

The ADS7842 is a complete, 4-channel, 12-bit Analog-to-Digital Converter (ADC). It contains a 12-bit, capacitor-based, Successive Approximation Register (SAR) ADC with a sample-and-hold amplifier, interface for microprocessor use, and parallel, 3-state output drivers. The ADS7842 is specified at a 200kHz sampling rate while dissipating only 2mW of power. The reference voltage can be varied from 100mV to V_{CC} with a corresponding LSB resolution from 24 μ V to 1.22mV. The ADS7842 is tested down to 2.7V operation.

Low power, high speed, and an onboard multiplexer make the ADS7842 ideal for battery-operated systems such as portable, multi-channel dataloggers and measurement equipment. The ADS7842 is available in an SSOP-28 package and is tested over the -40° C to $+85^{\circ}$ C temperature range.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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PACKAGE/ORDERING INFORMATION

PRODUCT	MINIMUM RELATIVE ACCURACY (LSB)	SINAD (dB)	PACKAGE-LEAD	PACKAGE DESIGNATOR ⁽¹⁾	SPECIFIED TEMPERATURE RANGE	PACKAGE MARKING	ORDERING NUMBER	TRANSPORT MEDIA, QUANTITY
ADS7842E	±2 "	68	SSOP-28	DB "	-40°C to +85°C	ADS7842E	ADS7842E ADS7842E/1K	Rails, 48 Tape and Reel, 1000
ADS7842EB	±1 "	70 "	SSOP-28	DB "	-40°C to +85°C	ADS7842EB	ADS7842EB ADS7842EB/1K	Rails, 48 Tape and Reel, 1000

NOTE: (1) For the most current specifications and package information, refer to our web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS(1)

+V _{CC} to GND	0.3V to +6V
Analog Inputs to GND	$-0.3V$ to $+V_{CC} + 0.3V$
Digital Inputs to GND	0.3V to +6V
Power Dissipation	250mW
Maximum Junction Temperature	+150°C
Operating Temperature Range	40°C to +85°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

NOTE: (1) Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods may affect device reliability.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

PIN CONFIGURATION

PIN DESCRIPTIONS

AlNO Analog Input Channel 0 AlN1 Analog Input Channel 1 AlN2 Analog Input Channel 2 AlN3 Analog Input Channel 2 AlN3 Analog Input Channel 3 Voltage Reference Input. See Electrical Characteristics Tables for ranges. AGND Analog Ground Data Bit 1 (MSB) Data Bit 1 (MSB) Data Bit 9 Data Bit 8 Data Data Bit 6 Data Bit 5 Data Bit 5 Data Bit 5 Data Bit 5 Data Bit 3 Data Bit 3 Data Bit 2 Data Bit 1 DBO Data Bit 2 Data Bit 1 DBO Data Bit 1 DBO Data Bit 1 DBO Data Bit 1 DBO Data Bit 2 Data Bit 1 DBO Data Bit 1 DBO Data Bit 1 DBO Data Bit 1 DBO Data Bit 0 CS Chip Select Input. Active LOW. The combination of CS taken LOW and With Taken LOW initiates a new conversion and places the outputs in the tri-state mode. Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY Gos LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and Wirt. The address inputs are latched on the rising edge of either RD or Wire. Al AO Channel Selected O O AINO O I AIN1 1 O AIN12 1 1 AIN13 D Digital Supply Input. Nominally +5V. Analog Supply Input. Nominally +5V.	PIN	NAME	DESCRIPTION
Analog Input Channel 2 Analog Input Channel 3 VREF Voltage Reference Input. See Electrical Characteristics Tables for ranges. AGND Analog Ground DB11 Data Bit 11 (MSB) DB9 DB9 Data Bit 9 DB9 Data Bit 9 DB9 Data Bit 6 DB10 DB8 Data Bit 6 DB10 DB8 Data Bit 5 DB10 DB9 Data Bit 6 DB10 DB8 DB10 DB10 DB10 DB10 DB10 DB10 DB10 DB10	1	AIN0	Analog Input Channel 0
A AlN3 Analog Input Channel 3 Voltage Reference Input. See Electrical Characteristics Tables for ranges. AGND Analog Ground Data Bit 11 (MSB) Data Bit 10 Data Bit 10 Data Bit 10 Data Bit 8 Data Bit 9 Data Bit 7 Data Bit 5 Data Bit 5 Data Bit 5 Data Bit 5 Data Bit 4 Dand Data Bit 1 DB7 Data Bit 4 DB8 Data Bit 3 DB9 Data Bit 3 DB9 Data Bit 1 DB0 Data Bit 1 DB0 Data Bit 1 DB1 Data Bit 1 DB2 Data Bit 2 DB3 Data Bit 2 DB4 Data Bit 1 DB0 Data Bit 0 (LSB) Read Input. Active LOW. Reads the data outputs in combination with CS. Chip Select Input. Active LOW initiates a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY Goes LOW and stays LOW during a conversion rate by the equation f _{CLK} = 16 • f _{SAMP-LE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected O O AIN0 O 1 AIN1 1 O AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	2	AIN1	Analog Input Channel 1
VREF Voltage Reference Input. See Electrical Characteristics Tables for ranges. AGND Analog Ground DB11 Data Bit 11 (MSB) DB10 Data Bit 10 DB9 Data Bit 9 DB9 Data Bit 9 DB9 Data Bit 8 DB10 DB8 Data Bit 7 DB1 DB8 Data Bit 6 DB7 Data Bit 5 DB6 Data Bit 6 DB7 Data Bit 5 DB8 Data Bit 5 DB9 Data Bit 5 DB9 Data Bit 6 DB9 Data Bit 7 DB9 Data Bit 7 DB9 Data Bit 1 DB9 Data Bit 1 DB9 Data Bit 1 DB0 Data Bit 1 DB0 Data Bit 0 (LSB) Read Input. Active LOW. Reads the data outputs in combination with CS. Chip Select Input. Active LOW initiates a new conversion and places the outputs in the tri-state mode. Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY Goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected O O AINO O 1 AIN1 1 O AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	3	AIN2	Analog Input Channel 2
tics Tables for ranges. AGND Analog Ground Data Bit 11 (MSB) DB10 Data Bit 10 DB9 DB9 Data Bit 9 DB9 Data Bit 9 DB7 Data Bit 7 DB8 Data Bit 6 DB7 Data Bit 5 DB8 Data Bit 5 DB8 Data Bit 5 DB9 Data Bit 5 DB9 Data Bit 5 DB9 Data Bit 6 DB9 Data Bit 6 DB9 Data Bit 6 DB9 Data Bit 6 DB9 Data Bit 7 DB9 Data Bit 1 DB9 Data Bit 1 DB0 Data Bit 2 DB1 Data Bit 1 DB2 Data Bit 1 DB0 Data Bit 0 (LSB) Read Input. Active LOW. Reads the data outputs in combination with CS. Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY BUSY Goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected O O AINO O 1 AIN1 1 O AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	4	AIN3	Analog Input Channel 3
DB11 Data Bit 11 (MSB) DB10 Data Bit 10 DB8 Data Bit 9 DB8 Data Bit 8 DB7 Data Bit 7 DB6 Data Bit 6 DB5 Data Bit 5 DB5 Data Bit 5 DB6 Data Bit 6 DB7 Data Bit 5 DB8 Data Bit 10 DB8 Data Bit 5 DB9 Data Bit 5 DB9 Data Bit 5 DB9 Data Bit 6 DB1 Data Bit 1 DB0 Data Bit 2 DB1 Data Bit 1 DB0 Data Bit 0 (LSB) Read Input. Active LOW. Reads the data outputs in combination with CS. Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY Goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected O AINO O 1 AIN1 1 O AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	5	V _{REF}	-
B DB10 Data Bit 10 Data Bit 9 Data Bit 9 Data Bit 7 Data Bit 7 Data Bit 6 Data Bit 5 Data Data Bit 5 Data Data Bit 5 Data Data Data Bit 5 Data Data Data Data Data Data Data Data	6	AGND	Analog Ground
9 DB9 Data Bit 9 10 DB8 Data Bit 8 11 DB7 Data Bit 8 11 DB7 Data Bit 7 12 DB6 Data Bit 6 13 DB5 Data Bit 5 14 DGND Digital Ground 15 DB4 Data Bit 4 16 DB3 Data Bit 3 17 DB2 Data Bit 2 18 DB1 Data Bit 1 19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . 25, 26 A0, A1 Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	7	DB11	Data Bit 11 (MSB)
10 DB8 Data Bit 8 11 DB7 Data Bit 7 12 DB6 Data Bit 6 13 DB5 Data Bit 5 14 DGND Digital Ground 15 DB4 Data Bit 4 16 DB3 Data Bit 3 17 DB2 Data Bit 2 18 DB1 Data Bit 1 19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . 25, 26 A0, A1 Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	8	DB10	Data Bit 10
11 DB7 Data Bit 7 12 DB6 Data Bit 6 13 DB5 Data Bit 5 14 DGND Digital Ground 15 DB4 Data Bit 4 16 DB3 Data Bit 3 17 DB2 Data Bit 2 18 DB1 Data Bit 1 19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	9	DB9	Data Bit 9
12 DB6 Data Bit 6 13 DB5 Data Bit 5 14 DGND Digital Ground 15 DB4 Data Bit 4 16 DB3 Data Bit 3 17 DB2 Data Bit 2 18 DB1 Data Bit 1 19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY Goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	10	DB8	Data Bit 8
13 DB5 Data Bit 5 14 DGND Digital Ground 15 DB4 Data Bit 4 16 DB3 Data Bit 3 17 DB2 Data Bit 2 18 DB1 Data Bit 1 19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . 25, 26 A0, A1 Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	11	DB7	Data Bit 7
14 DGND Digital Ground 15 DB4 Data Bit 4 16 DB3 Data Bit 3 17 DB2 Data Bit 2 18 DB1 Data Bit 1 19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . 25, 26 A0, A1 Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	12	DB6	Data Bit 6
Data Bit 4 Data Bit 3 Data Bit 2 Data Bit 2 Data Bit 0 (LSB) Read Input. Active LOW. Reads the data outputs in combination with CS. Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY BUSY BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1	13	DB5	Data Bit 5
16 DB3 Data Bit 3 17 DB2 Data Bit 2 18 DB1 Data Bit 1 19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . 25, 26 A0, A1 Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	14	DGND	Digital Ground
Data Bit 2 Data Bit 2 Data Bit 1 DB0 Data Bit 0 (LSB) Read Input. Active LOW. Reads the data outputs in combination with CS. Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected O AINO O 1 AIN1 1 O AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	15	DB4	Data Bit 4
18 DB1 Data Bit 1 19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 ● f _{SAMPLE} . 25, 26 A0, A1 Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	16	DB3	Data Bit 3
19 DB0 Data Bit 0 (LSB) 20 RD Read Input. Active LOW. Reads the data outputs in combination with CS. 21 CS Chip Select Input. Active LOW. The combination of CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. 22 WR Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. 23 BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . 25, 26 A0, A1 Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	17	DB2	Data Bit 2
Read Input. Active LOW. Reads the data outputs in combination with \$\overline{CS}\$. Chip Select Input. Active LOW. The combination of \$\overline{CS}\$ taken LOW and \$\overline{WR}\$ taken LOW initiates a new conversion and places the outputs in the tri-state mode. Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with \$\overline{CS}\$. BUSY BUSY goes LOW and stays LOW during a conversion. \$\overline{BUSY}\$ rises when a conversion is complete and enables the parallel outputs. CLK External Clock Input. The clock speed determines the conversion rate by the equation \$f_{CLK} = 16 \cdot f_{SAMPLE}\$. Address Inputs. Selects one of four analog input channels in combination with \$\overline{CS}\$ and \$\overline{WR}\$. The address inputs are latched on the rising edge of either \$\overline{RD}\$ or \$\overline{WR}\$. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	18	DB1	Data Bit 1
combination with \(\overline{\text{CS}}\). Chip Select Input. Active LOW. The combination of \(\overline{\text{CS}}\) taken LOW and \(\overline{\text{WR}}\) taken LOW initiates a new conversion and places the outputs in the tri-state mode. Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with \(\overline{\text{CS}}\). BUSY goes LOW and stays LOW during a conversion. \(\overline{\text{BUSY}}\) gises when a conversion is complete and enables the parallel outputs. CLK External Clock Input. The clock speed determines the conversion rate by the equation \(f_{\text{CLK}} = 16 \cdot \mathbf{f}_{\text{SAMPLE}}\). Address Inputs. Selects one of four analog input channels in combination with \(\overline{\text{CS}}\) and \(\overline{\text{WR}}\). The address inputs are latched on the rising edge of either \(\overline{\text{RD}}\) or \(\overline{\text{WR}}\). A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	19	DB0	Data Bit 0 (LSB)
CS taken LOW and WR taken LOW initiates a new conversion and places the outputs in the tri-state mode. Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected O AINO O 1 AIN1 1 O AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	20	RD	· ·
Write Input. Active LOW. Starts a new conversion and selects an analog channel via address inputs A0 and A1, in combination with CS. BUSY BUSY goes LOW and stays LOW during a conversion. BUSY rises when a conversion is complete and enables the parallel outputs. CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected O AINO O 1 AIN1 1 O AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	21	CS	$\overline{\text{CS}}$ taken LOW and $\overline{\text{WR}}$ taken LOW initiates a new conversion and places the outputs in the tri-state
conversion. BUSY rises when a conversion is complete and enables the parallel outputs. 24 CLK External Clock Input. The clock speed determines the conversion rate by the equation f _{CLK} = 16 • f _{SAMPLE} . 25, 26 A0, A1 Address Inputs. Selects one of four analog input channels in combination with CS and WR. The address inputs are latched on the rising edge of either RD or WR. A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 27 V _{DIG} Digital Supply Input. Nominally +5V.	22	WR	and selects an analog channel via address inputs A0
conversion rate by the equation $f_{CLK} = 16 \cdot f_{SAMPLE}$. Address Inputs. Selects one of four analog input channels in combination with \overline{CS} and \overline{WR} . The address inputs are latched on the rising edge of either \overline{RD} or \overline{WR} . A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 Digital Supply Input. Nominally +5V.	23	BUSY	conversion. BUSY rises when a conversion is
channels in combination with \overline{CS} and \overline{WR} . The address inputs are latched on the rising edge of either \overline{RD} or \overline{WR} . A1 A0 Channel Selected 0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 27 V _{DIG} Digital Supply Input. Nominally +5V.	24	CLK	
0 0 AIN0 0 1 AIN1 1 0 AIN2 1 1 AIN3 27 V _{DIG} Digital Supply Input. Nominally +5V.	25, 26	A0, A1	channels in combination with $\overline{\text{CS}}$ and $\overline{\text{WR}}$. The address inputs are latched on the rising edge of
0 1 AIN1 1 0 AIN2 1 1 1 AIN3 27 V _{DIG} Digital Supply Input. Nominally +5V.			A1 A0 Channel Selected
1 0 AIN2 1 1 AIN3 27 V _{DIG} Digital Supply Input. Nominally +5V.			0 0 AIN0
1 1 AIN3 27 V _{DIG} Digital Supply Input. Nominally +5V.			0 1 AIN1
27 V _{DIG} Digital Supply Input. Nominally +5V.			1 0 AIN2
			1 1 AIN3
	27	V _{DIG}	Digital Supply Input. Nominally +5V.
	28	V _{ANA}	Analog Supply Input. Nominally +5V.



ELECTRICAL CHARACTERISTICS: +5V

At $T_A = -40^{\circ}\text{C}$ to +85°C, +V_{CC} = +5V, V_{REF} = +5V, f_{SAMPLE} = 200kHz, and f_{CLK} = 16 • f_{SAMPLE} = 3.2MHz, unless otherwise noted.

			ADS7842E		,	ADS7842EI	В	
PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
RESOLUTION				12			*	Bits
ANALOG INPUT Full-Scale Input Span Capacitance Leakage Current		0	25 ±1	V _{REF}	*	*	*	V pF μA
SYSTEM PERFORMANCE No Missing Codes Integral Linearity Error Differential Linearity Error Offset Error Offset Error Match Gain Error Gain Error Match Noise Power-Supply Rejection		12	±0.8 0.15 0.1 30 70	±2 ±3 1.0 ±4 1.0	*	±0.5 * * * *	±1 ±1 * * ±3 *	Bits LSB(1) LSB LSB LSB LSB LSB LSB LSB LSB
SAMPLING DYNAMICS Conversion Time Acquisition Time Throughput Rate Multiplexer Settling Time Aperture Delay Aperture Jitter		3	500 30 100	12 200	*	* * *	*	Clk Cycles Clk Cycles kHz ns ns
DYNAMIC CHARACTERISTICS Total Harmonic Distortion ⁽²⁾ Signal-to-(Noise + Distortion) Spurious-Free Dynamic Range Channel-to-Channel Isolation	V_{IN} = 5Vp-p at 10kHz V_{IN} = 5Vp-p at 10kHz V_{IN} = 5Vp-p at 10kHz V_{IN} = 5Vp-p at 50kHz	68 72	-78 71 79 120	-72	70 76	-80 72 81 *	-76	dB dB dB dB
REFERENCE INPUT Range Resistance Input Current	DCLK Static f _{SAMPLE} = 12.5kHz DCLK Static	0.1	5 40 2.5 0.001	+V _{cc} 100	*	* * *	* *	V GΩ μΑ μΑ μΑ
DIGITAL INPUT/OUTPUT Logic Family Logic Levels V _{IH} V _{IL} V _{OH} V _{OL} Data Format External Clock	$ I_{IH} \le +5\mu A$ $ I_{IL} \le +5\mu A$ $I_{OH} = -250\mu A$ $I_{OL} = 250\mu A$	3.0 -0.3 3.5 S	CMOS traight Bina	5.5 +0.8 0.4 ry 3.2	* * *	*	* * *	V V V V
POWER-SUPPLY REQUIREMENTS +V _{CC} Quiescent Current Power Dissipation	Specified Performance $f_{SAMPLE} = 12.5 kHz$ Power-Down Mode ⁽³⁾ , $\overline{CS} = +V_{CC}$	4.75	550 300	5.25 900 3 4.5	*	*	* * *	V μΑ μΑ μΑ mW
TEMPERATURE RANGE Specified Performance		-40		+85	*		*	°C

^{*} Same specifications as ADS7842E.

NOTES: (1) LSB means Least Significant Bit. With V_{REF} equal to +5.0V, one LSB is 1.22mV.

- (2) First five harmonics of the test frequency.
 (3) Power-down mode at end of conversion when WR, CS, and BUSY conditions have all been met. Refer to Table III of this data sheet.



ELECTRICAL CHARACTERISTICS: +2.7V

At $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $+V_{CC} = +2.7\text{V}$, $V_{REF} = +2.5\text{V}$, $f_{SAMPLE} = 125\text{kHz}$, and $f_{CLK} = 16 \bullet f_{SAMPLE} = 2\text{MHz}$, unless otherwise noted.

			ADS7842E		4	ADS7842EI	3	
PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
RESOLUTION				12			*	Bits
ANALOG INPUT Full-Scale Input Span Capacitance Leakage Current		0	25 ±1	V_{REF}	*	*	*	V pF μA
SYSTEM PERFORMANCE No Missing Codes Integral Linearity Error Differential Linearity Error Offset Error Offset Error Gain Error Gain Error Match Noise Power-Supply Rejection		12	±0.8 0.15 0.1 30 70	±2 ±5 1.0 ±4 1.0	*	±0.5 * * * *	±1 ±1 * * ±3 *	Bits LSB(1) LSB LSB LSB LSB LSB LSB LSB LSB dSB MVrms dB
SAMPLING DYNAMICS Conversion Time Acquisition Time Throughput Rate Multiplexer Settling Time Aperture Delay Aperture Jitter		3	500 30 100	12 125	*	* * *	*	Clk Cycles Clk Cycles kHz ns ns
DYNAMIC CHARACTERISTICS								<u> </u>
Total Harmonic Distortion(2)	$3.6V \ge V_{CC} \ge 3.0V, V_{IN} = 2.5Vp-p$ at 10kHz		-77	-70		-79	-74	dB
	$3.0V > V_{CC} \ge 2.7V, V_{IN} = 2.5Vp-p$ at 10kHz		-77	-70		*	*	dB
Signal-to-(Noise + Distortion)	$3.6V \ge V_{CC} \ge 3.0V, V_{IN} = 2.5Vp-p$ at 10kHz	68	71		70	72		dB
	$3.0V > V_{CC} \ge 2.7V, V_{IN} = 2.5Vp-p$ at 10kHz	68	71		*	*		dB
Spurious-Free Dynamic Range	$3.6V \ge V_{CC} \ge 3.0V, V_{IN} = 2.5Vp-p$ at 10kHz	72	78		76	80		dB
	$3.0V > V_{CC} \ge 2.7V, V_{IN} = 2.5Vp-p$ at 10kHz	72	78		*	*		dB
Channel-to-Channel Isolation	$V_{IN} = 2.5Vp-p$ at $50kHz$		100			*		dB
REFERENCE INPUT Range Resistance Input Current	DCLK Static f _{SAMPLE} = 12.5kHz DCLK Static	0.1	5 13 2.5 0.001	+V _{CC} 40 3	*	* * *	* *	V GΩ μΑ μΑ μΑ
DIGITAL INPUT/OUTPUT Logic Family Logic Levels V _{IH} V _{IL} V _{OH} V _{OL} Data Format External Clock	I _{IH} ≤ +5μΑ I _{IL} ≤ +5μΑ Ι _{ΟΗ} = −250μΑ Ι _{ΟL} = 250μΑ	+V _{CC} • 0.7 -0.3 +V _{CC} • 0.8 St	CMOS	5.5 +0.8 0.4 ry 2	* * *	*	* * *	V V V V
POWER-SUPPLY REQUIREMENTS +V _{CC} Quiescent Current	Specified Performance $f_{SAMPLE} = 12.5 kHz$ Power-Down Mode ⁽³⁾ , $\overline{CS} = +V_{CC}$	2.7	280 220	3.6 650	*	*	* *	V μΑ μΑ μΑ
Power Dissipation				1.8			*	mW
TEMPERATURE RANGE Specified Performance		-40		+85	*		*	°c

 $[\]ensuremath{\boldsymbol{\ast}}$ Same specifications as ADS7842E.

⁽³⁾ Power-down mode at end of conversion when WR, CS, and BUSY conditions have all been met. Refer to Table III of this data sheet.

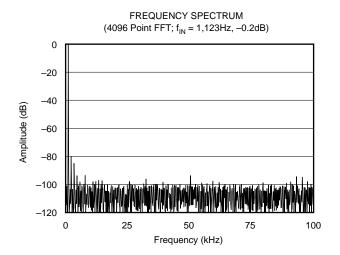


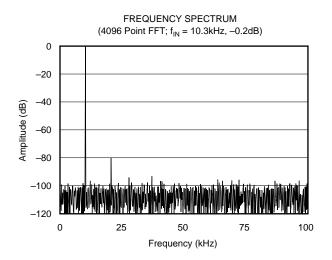
NOTES: (1) LSB means Least Significant Bit. With $\rm V_{REF}$ equal to +2.5V, one LSB is 610mV.

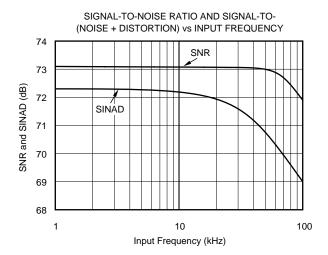
⁽²⁾ First five harmonics of the test frequency.

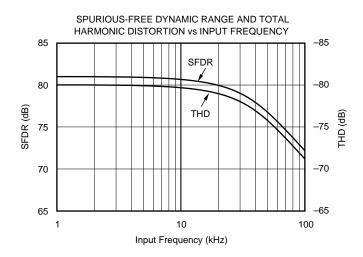
TYPICAL CHARACTERISTICS: +5V

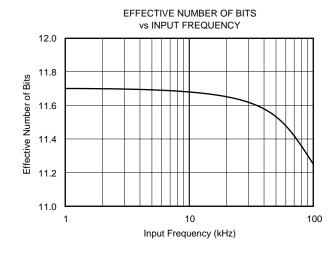
At T_A = +25°C, + V_{CC} = +5V, V_{REF} = +5V, f_{SAMPLE} = 200kHz, and f_{CLK} = 16 • f_{SAMPLE} = 3.2MHz, unless otherwise noted.

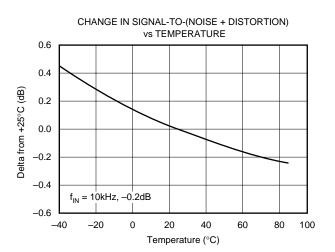








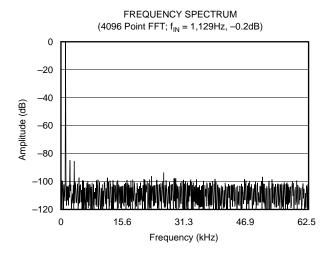


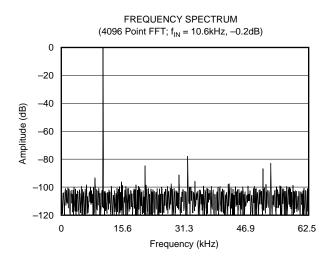


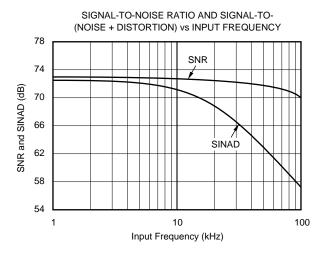


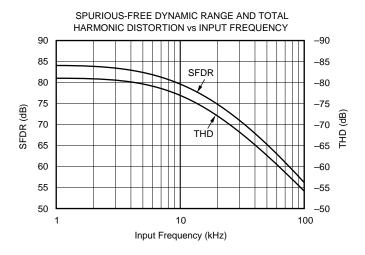
TYPICAL CHARACTERISTICS: +2.7V

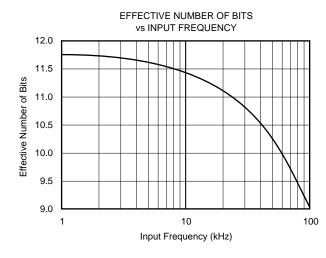
At $T_A = +25^{\circ}\text{C}$, $+V_{CC} = +2.7\text{V}$, $V_{REF} = +2.5\text{V}$, $f_{SAMPLE} = 125\text{kHz}$, and $f_{CLK} = 16 \bullet f_{SAMPLE} = 2\text{MHz}$, unless otherwise noted.

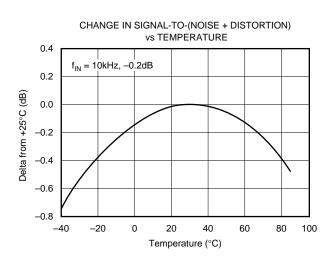






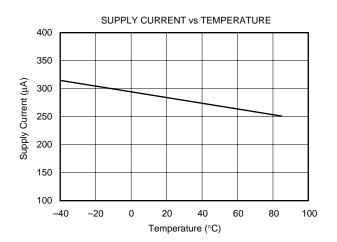


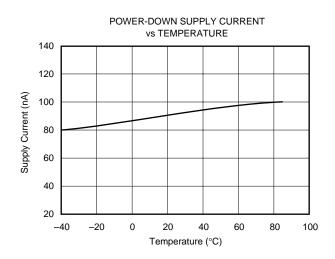


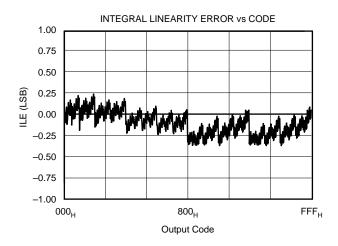


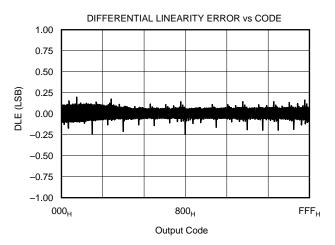
TYPICAL CHARACTERISTICS: +2.7V (Continued)

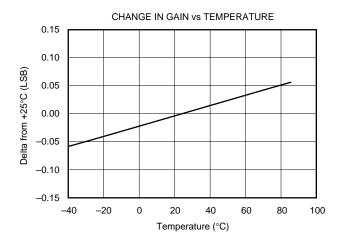
At $T_A = +25^{\circ}C$, $+V_{CC} = +2.7V$, $V_{REF} = +2.5V$, $f_{SAMPLE} = 125kHz$, and $f_{CLK} = 16 \bullet f_{SAMPLE} = 2MHz$, unless otherwise noted.

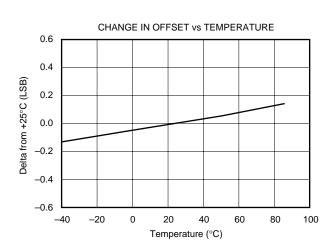






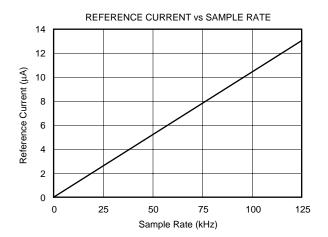


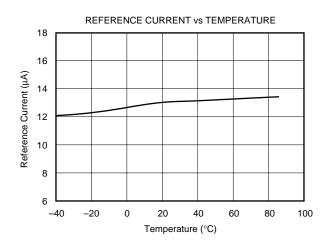


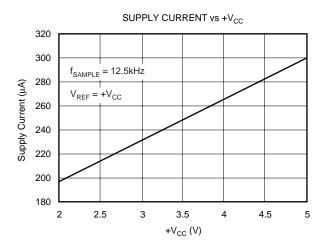


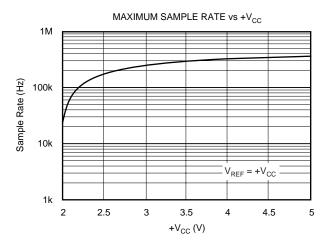
TYPICAL CHARACTERISTICS: +2.7V (Continued)

At $T_A = +25^{\circ}\text{C}$, $+V_{CC} = +2.7\text{V}$, $V_{REF} = +2.5\text{V}$, $f_{SAMPLE} = 125\text{kHz}$, and $f_{CLK} = 16 \bullet f_{SAMPLE} = 2\text{MHz}$, unless otherwise noted.









THEORY OF OPERATION

The ADS7842 is a classic SAR ADC. The architecture is based on capacitive redistribution which inherently includes a sample-and-hold function. The converter is fabricated on a $0.6\mu m$ CMOS process.

The basic operation of the ADS7842 is shown in Figure 1. The device requires an external reference and an external clock. It operates from a single supply of 2.7V to 5.25V. The external reference can be any voltage between 100mV and $+V_{CC}$. The value of the reference voltage directly sets the input range of the converter. The average reference input current depends on the conversion rate of the ADS7842.

ANALOG INPUTS

The ADS7842 features four, single-ended inputs. The input current into each analog input depends on input voltage and sampling rate. Essentially, the current into the device must charge the internal hold capacitor during the sample period. After this capacitance has fully charged, there is no further input current. The source of the analog input voltage must be able to charge the input capacitance to a 12-bit settling level within the same period, which can be as little as 350ns in

some operating modes. While the converter is in the hold mode, or after the sampling capacitor has been fully charged, the input impedance of the analog input is greater than $1G\Omega$.

EXTERNAL CLOCK

The ADS7842 requires an external clock to run the conversion process. This clock can vary between 200kHz (12.5kHz throughput) and 3.2MHz (200kHz throughput). The duty cycle of the clock is unimportant as long as the minimum HIGH and LOW times are at least 150ns and the clock period is at least 300ns. The minimum clock frequency is set by the leakage on the capacitors internal to the ADS7842.

BASIC OPERATION

Figure 1 shows the simple circuit required to operate the ADS7842 with Channel 0 selected. A conversion can be initiated by bringing the $\overline{\text{WR}}$ pin (pin 22) LOW for a minimum of 25ns. $\overline{\text{BUSY}}$ (pin 23) will output a LOW during the conversion process and rises only after the conversion is complete. The 12 bits of output data will be valid on pins 7-13 and 15-19 following the rising edge of $\overline{\text{BUSY}}$.

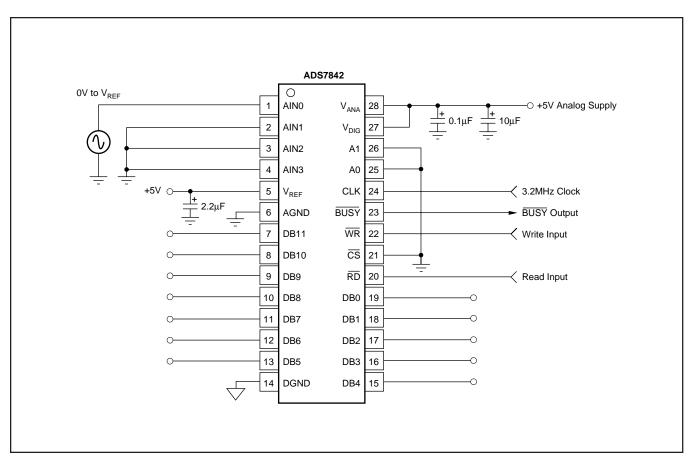


FIGURE 1. Basic Operation of the ADS7842.

STARTING A CONVERSION

A conversion is initiated on the falling edge of the WR input, with valid signals on A0, A1, and CS. The ADS7842 will enter the conversion mode on the first rising edge of the external clock following the WR pin going LOW. The ADS7842 will start the conversion on the 1st clock cycle. The MSB will be approximated by the Capacitive Digital-to-Analog Converter (CDAC) on the 1st clock cycle, the 2nd-MSB on the 2nd cycle, and so on until the LSB has been decided on the 12th clock cycle. The BUSY output will go LOW 20ns after the falling edge of the WR pin. The BUSY output will return HIGH just after the ADS7842 has finished a conversion and the data will be valid on pins 7-13, 15-19. The rising edge of BUSY can be used to latch the data. It is recommended that the data be read immediately after each conversion. The switching noise of the asynchronous data transfer can cause digital feedthrough degrading the converter's performance. See Figure 2.

READING DATA

Data from the ADS7842 will appear at pins 7-13 and 15-19. The MSB will output on pin 7 while the LSB will output on pin 19. The outputs are coded in Straight Binary (with 0V = 000_H and V_{REF} = FFF $_H$, see Table IV). Following a conversion, the \overline{BUSY} pin will go HIGH. After \overline{BUSY} goes HIGH, the \overline{CS} and \overline{RD} pins may be brought LOW to enable the 12-bit output bus. \overline{CS} and \overline{RD} must be held LOW for at least 25ns seconds following \overline{BUSY} HIGH. Data will be valid 25ns seconds after the falling edge of both \overline{CS} and \overline{RD} . The output data will remain valid for 25ns seconds following the rising edge of both \overline{CS} and \overline{RD} . See Figure 4 for the read cycle timing diagram.

POWER-DOWN MODE

The ADS7842 incorporates a unique method of placing the ADC in the power-down mode. Rather than adding an extra pin to the package, the A0 address pin is used in conjunction with the \overline{RD} pin to place the device in power-down mode and also to 'wake-up' the ADC following power-down. In this shutdown mode, all analog and digital circuitry is turned off. The simplest way to place the ADS7842 in power-down mode is immediately following a conversion. After a conversion has been completed and the \overline{BUSY} output has returned HIGH, \overline{CS} and \overline{RD} must be brought LOW for a minimum of 25ns. While keeping \overline{CS} LOW, \overline{RD} is brought HIGH and the ADS7842 enters the power-down mode, provided the A0 pin is HIGH (see Figure 5 and Table III). In order to 'wake-up' the device following power-down, A0 must be LOW when \overline{RD} switches from LOW to HIGH a second time (see Figure 6).

The typical supply current of the ADS7842 with a 5V supply and 200kHz sampling rate is $550\mu A$. In the power-down mode the current is typically reduced to $3\mu A$.

SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNITS
t _{CONV}	Conversion Time			6.5	μs
t_{ACQ}	Acquisition Time			1.5	μs
t_{CKP}	Clock Period	500			ns
t _{CKL}	Clock LOW	150			ns
t _{CKH}	Clock HIGH	150			ns
t ₁	CS to WR/RD Setup Time	0			ns
t ₂	Address to CS Hold Time	0			ns
t ₃	CS LOW	25			ns
t ₄	CLK to WR Setup Time	25			ns
t ₅	CS to BUSY LOW			20	ns
t ₆	CLK to WR LOW	5			ns
t ₇	CLK to WR HIGH	25			ns
t ₈	WR to CLK HIGH	25			ns
t ₉	Address Hold Time	5			ns
t ₁₀	Address Setup Time	5			ns
t ₁₁	BUSY to RD Delay	0			ns
t ₁₂	CLK LOW to BUSY HIGH	10			ns
t ₁₃	BUS Access	25			ns
t ₁₄	BUS Relinguish	25			ns
t ₁₅	Address to RD HIGH	2			ns
t ₁₆	Address Hold Time	2			ns
t ₁₇	RD HIGH to CLK LOW	50			ns

TABLE I. Timing Specifications (+V $_{CC}$ = +2.7V to 3.6V, T_A = -40°C to +85°C, C_{LOAD} = 50pF).

SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNITS
t _{CONV}	Conversion Time			3.5	μs
t _{ACQ}	Acquisition Time			1.5	μs
t _{CKP}	Clock Period	300			ns
t _{CKL}	Clock LOW	150			ns
t _{CKH}	Clock HIGH	150			ns
t ₁	CS to WR/RD Setup Time	0			ns
t ₂	Address to CS Hold Time	0			ns
t ₃	CS LOW	25			ns
t ₄	CLK to WR Setup Time	25			ns
t ₅	CS to BUSY LOW			20	ns
t ₆	CLK to WR LOW	5			ns
t ₇	CLK to WR HIGH	25			ns
t ₈	WR to CLK HIGH	25			ns
t ₉	Address Hold Time	5			ns
t ₁₀	Address Setup Time	5			ns
t ₁₁	BUSY to RD Delay	0			ns
t ₁₂	CLK LOW to BUSY HIGH	10			ns
t ₁₃	BUS Access	25			ns
t ₁₄	BUS Relinquish	25			ns
t ₁₅	Address to RD HIGH	2			ns
t ₁₆	Address Hold Time	2			ns
t ₁₇	RD HIGH to CLK LOW	50			ns

TABLE II. Timing Specifications (+V_{CC} = +4.75V to +5.25V, $T_A = -40$ °C to +85°C, $C_{LOAD} = 50$ pF).



CS	RD	WR	BUSY	A0	A1	COMMENTS			
0	∡ X 1 1 X Power-Down Mode								
0	₽	Х	1	0	Х	Wake-Up Mode			
. F m	eans ris	sing ed	ge trigg	gered.)	K = Do	n't care.			

TABLE III. Truth Table for Power-Down and Wake-Up Modes.

		DIGITAL OUTPUT STRAIGHT BINARY				
DESCRIPTION	ANALOG INPUT	BINARY CODE	HEX CODE			
Least Significant Bit (LSB)	1.2207mV					
Full-Scale	4.99878V	1111 1111 1111	FFF			
Midscale	2.5V	1000 0000 0000	800			
Midscale -1LSB	2.49878V	0111 1111 1111	7FF			
Zero Full-Scale	0V	0000 0000 0000	000			

TABLE IV. Ideal Input Voltages and Output Codes ($V_{REF} = 5V$).

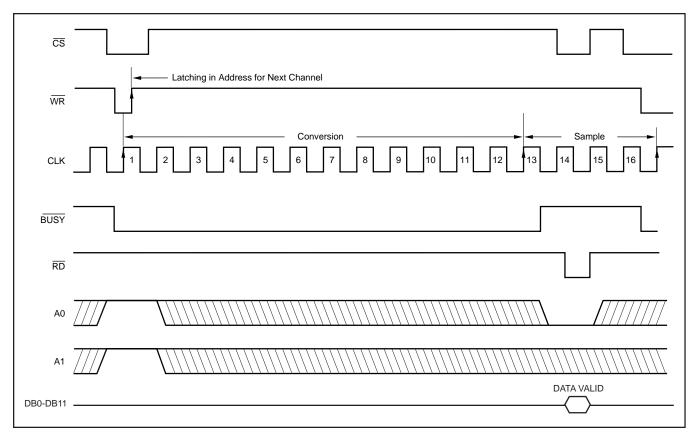


FIGURE 2. Normal Operation, 16 Clocks per Conversion.

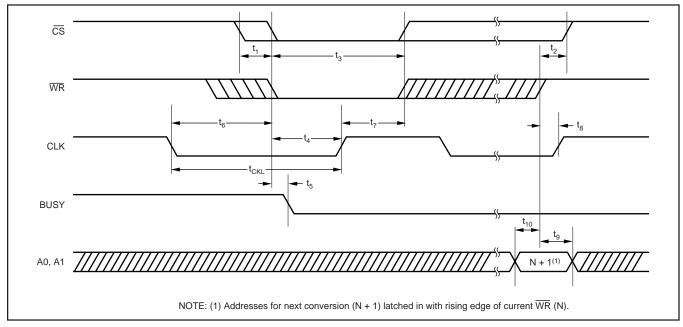


FIGURE 3. Initiating a Conversion.

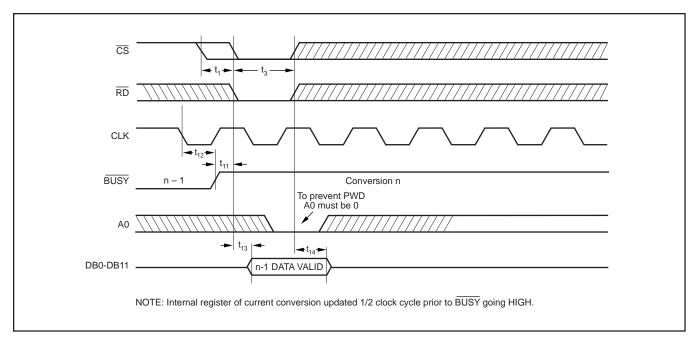


FIGURE 4. Read Timing Following a Conversion.

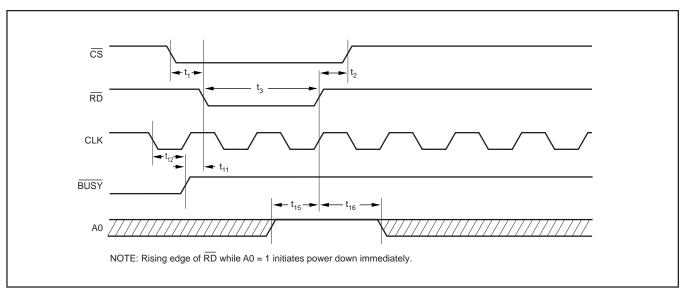


FIGURE 5. Entering Power-Down Using \overline{RD} and A0.

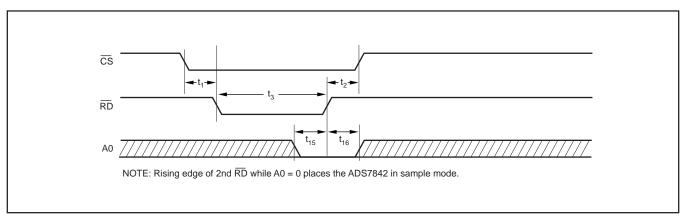


FIGURE 6. Initiating Wake-Up Using RD and A0.



REFERENCE INPUT

The external reference sets the analog input range. The ADS7842 will operate with a reference in the range of 100mV to $\pm V_{CC}$.

There are several critical items concerning the reference input and its wide voltage range. As the reference voltage is reduced, the analog voltage weight of each digital output code is also reduced. This is often referred to as the LSB size and is equal to the reference voltage divided by 4096. Any offset or gain error inherent in the ADC will appear to increase, in terms of LSB size, as the reference voltage is reduced. For example, if the offset of a given converter is 2LSBs with a 2.5V reference, then it will typically be 10LSBs with a 0.5V reference. In each case, the actual offset of the device is the same, 1.22mV.

Likewise, the noise or uncertainty of the digitized output will increase with lower LSB size. With a reference voltage of 100mV, the LSB size is $24\mu V$. This level is below the internal noise of the device. As a result, the digital output code will not be stable and vary around a mean value by a number of LSBs. The distribution of output codes will be gaussian and the noise can be reduced by simply averaging consecutive conversion results or applying a digital filter.

With a lower reference voltage, care should be taken to provide a clean layout including adequate bypassing, a clean (low-noise, low-ripple) power supply, a low-noise reference, and a low-noise input signal. Because the LSB size is lower, the converter will also be more sensitive to nearby digital signals and electromagnetic interference.

The voltage into the V_{REF} input is not buffered and directly drives the CDAC portion of the ADS7842. Typically, the input current is $13\mu A$ with a 2.5V reference. This value will vary by microamps depending on the result of the conversion. The reference current diminishes directly with both conversion rate and reference voltage. As the current from the reference is drawn on each bit decision, clocking the converter more quickly during a given conversion period will not reduce overall current drain from the reference.

Data Format

The ADS7842 output data is in Straight Offset Binary format, see Table IV. This table shows the ideal output code for the given input voltage and does not include the effects of offset, gain, or noise.

LAYOUT

For optimum performance, care should be taken with the physical layout of the ADS7842 circuitry. This is particularly true if the reference voltage is low and/or the conversion rate is high.

The basic SAR architecture is sensitive to glitches or sudden changes on the power supply, reference, ground connections, and digital inputs that occur just prior to latching the output of the analog comparator. Thus, during any single conversion for an n-bit SAR converter, there are n "windows" in which large external transient voltages can easily affect the conversion result. Such glitches might originate from switching power supplies, nearby digital logic, and high-power devices. The degree of error in the digital output depends on the reference voltage, layout, and the exact timing of the external event. The error can change if the external event changes in time with respect to the DCLK input.

With this in mind, power to the ADS7842 should be clean and well bypassed. A $0.1\mu F$ ceramic bypass capacitor should be placed as close to the device as possible. In addition, a $1\mu F$ to $10\mu F$ capacitor and a 5Ω or 10Ω series resistor may be used to low-pass filter a noisy supply.

The reference should be similarly bypassed with a $0.1\mu F$ capacitor. Again, a series resistor and large capacitor can be used to low-pass filter the reference voltage. If the reference voltage originates from an op amp, make sure that it can drive the bypass capacitor without oscillation (the series resistor can help in this case). The ADS7842 draws very little current from the reference on average, but it does place larger demands on the reference circuitry over short periods of time (on each rising edge of CLK during a conversion).

The ADS7842 architecture offers no inherent rejection of noise or voltage variation in regards to the reference input. This is of particular concern when the reference input is tied to the power supply. Any noise and ripple from the supply will appear directly in the digital results. While high frequency noise can be filtered out as discussed in the previous paragraph, voltage variation due to line frequency (50Hz or 60Hz) can be difficult to remove.

The GND pin should be connected to a clean ground point. In many cases, this will be the "analog" ground. Avoid connections which are too near the grounding point of a microcontroller or digital signal processor. If needed, run a ground trace directly from the converter to the power-supply entry point. The ideal layout will include an analog ground plane dedicated to the converter and associated analog circuitry.

Revision History

DATE	REVISION	PAGE	SECTION	DESCRIPTION
10/06	С	4	Electrical Characteristics	Dynamic Characteristics—total harmonic distortion: added new conditions.

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.







11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
ADS7842E	ACTIVE	SSOP	DB	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ADS7842E	Samples
ADS7842E/1K	ACTIVE	SSOP	DB	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		ADS7842E	Samples
ADS7842E/1KG4	ACTIVE	SSOP	DB	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		ADS7842E	Samples
ADS7842EB	ACTIVE	SSOP	DB	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		ADS7842E B	Samples
ADS7842EB/1K	ACTIVE	SSOP	DB	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		ADS7842E B	Samples
ADS7842EB/1KG4	ACTIVE	SSOP	DB	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		ADS7842E B	Samples
ADS7842EBG4	ACTIVE	SSOP	DB	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR		ADS7842E B	Samples
ADS7842EG4	ACTIVE	SSOP	DB	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ADS7842E	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



PACKAGE OPTION ADDENDUM

11-Apr-2013

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ADS7842E/1K	SSOP	DB	28	1000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
ADS7842EB/1K	SSOP	DB	28	1000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
ADS7842E/1K	SSOP	DB	28	1000	367.0	367.0	38.0	
ADS7842EB/1K	SSOP	DB	28	1000	367.0	367.0	38.0	

DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

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